

# **HAT2201WP**

# Silicon N Channel Power MOS FET Power Switching

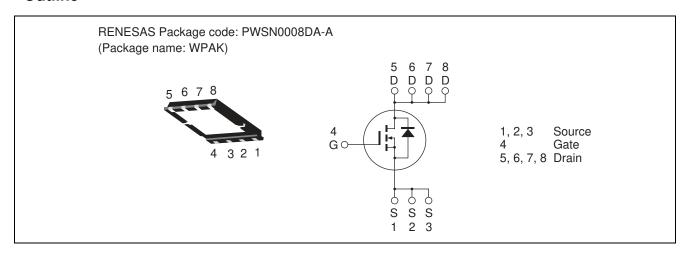
REJ03G1679-0310 Rev.3.10 May 21, 2010

#### **Features**

- Capable of 8 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} = 34 \text{ m}\Omega \text{ typ.}$  (at  $V_{GS} = 10 \text{ V}$ )

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	100	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	15	A
Drain peak current	I <sub>D(pulse)</sub> Note1	60	A
Body-drain diode reverse drain current	I <sub>DR</sub>	15	A
Avalanche current	I <sub>AP</sub> Note 2	15	A
Avalanche energy	E <sub>AR</sub> Note 2	22.5	mJ
Channel dissipation	Pch Note3	15	W
Channel to case thermal Impedance	θch-c Note3	8.33	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

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Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$ 

3.  $Tc = 25^{\circ}C$ 

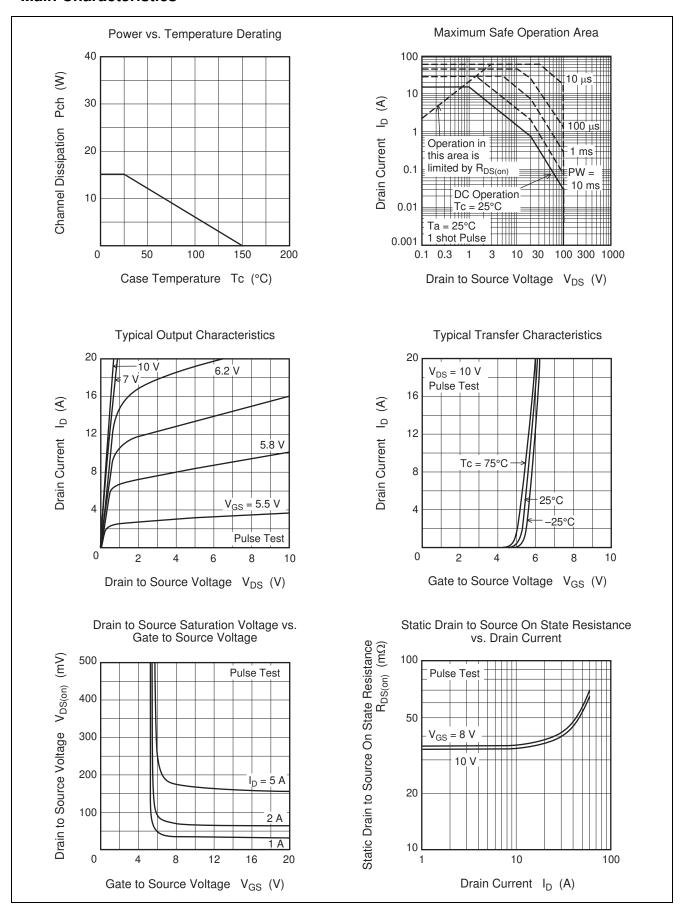
# **Electrical Characteristics**

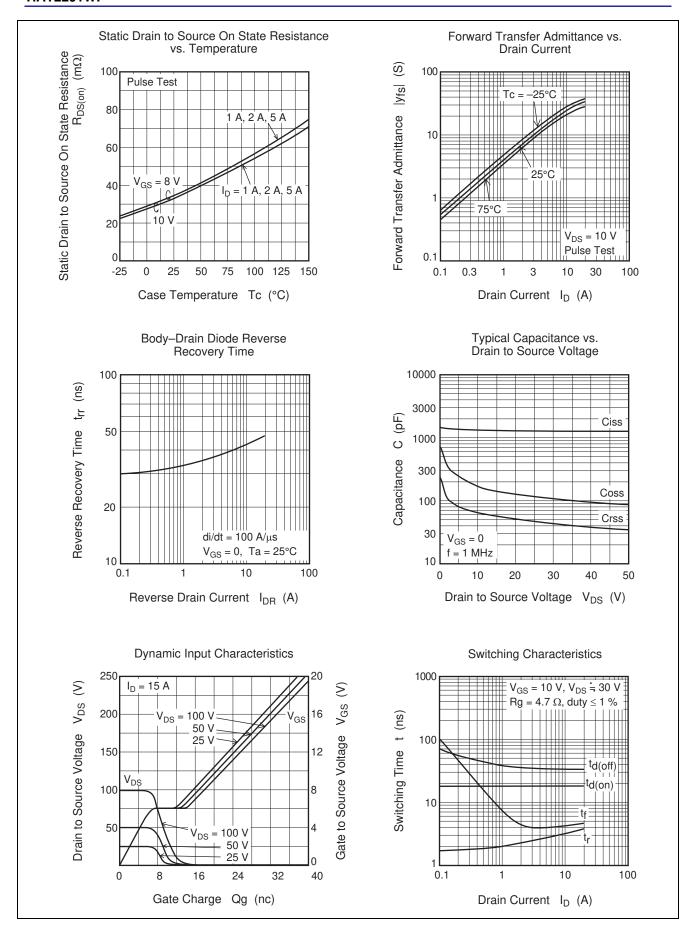
 $(Ta = 25^{\circ}C)$ 

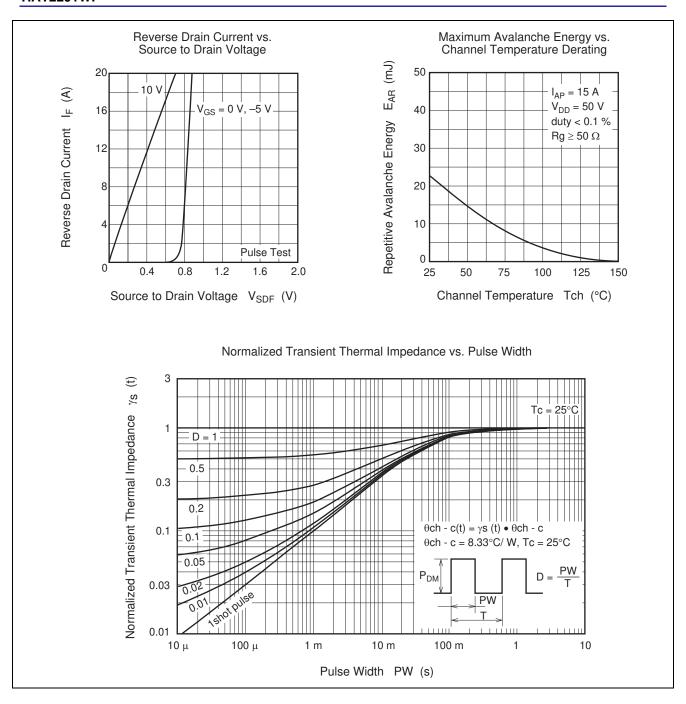
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μА	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 100 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.5	_	5.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	34	43	mΩ	$I_D = 7.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R <sub>DS(on)</sub>	_	35	49	mΩ	$I_D = 7.5 \text{ A}, V_{GS} = 8 \text{ V}^{Note4}$
Forward transfer admittance	y <sub>fs</sub>	12	20	_	S	$I_D = 7.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	1450	_	рF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	180	_	рF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	65	_	рF	f = 1 MHz
Gate resistance	Rg	_	0.9	_	Ω	
Total gate charge	Qg	_	21	_	nc	$V_{DD} = 50 \text{ V}$
Gate to source charge	Qgs	_	7.6	_	nc	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	5.2	_	nc	I <sub>D</sub> = 15 A
Turn-on delay time	t <sub>d(on)</sub>	_	18	_	ns	$V_{GS} = 10 \text{ V}, I_D = 7.5 \text{ A}$
Rise time	t <sub>r</sub>	_	3	_	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	t <sub>d(off)</sub>	_	33	_	ns	$R_L = 4 \Omega$
Fall time	t <sub>f</sub>	_	4.1	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	$V_{DF}$	_	0.84	1.10	V	$I_F = 15 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	45	_	ns	$I_F = 15 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/ \mu \text{s}$

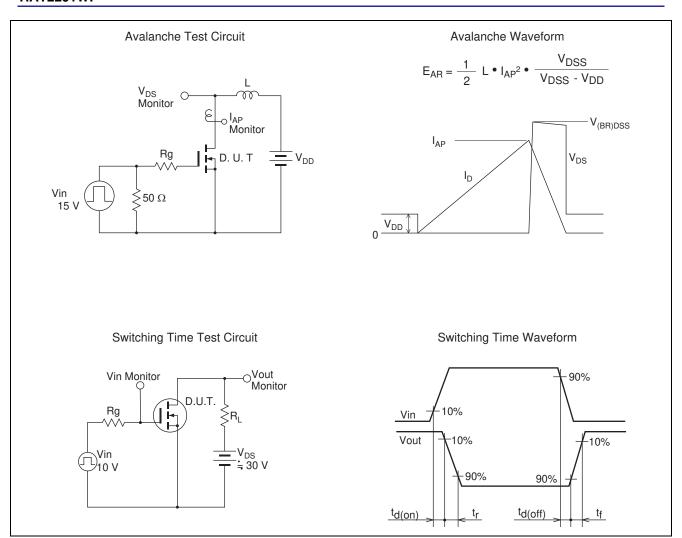
Notes: 4. Pulse test

#### **Main Characteristics**

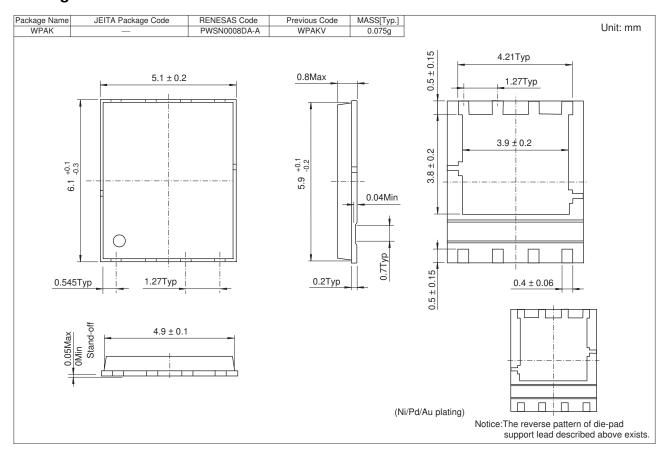








# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2201WP-EL-E	2500 pcs	Taping

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Renesas Electronics America Inc. 2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A. Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

เพลายอย อเชียงเทเชง **ทยายู nong Limited** Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong Tel: +852-2866-9318, Fax: +852-2866-9022/9044

Renesas Electronics Taiwan Co., Ltd.

7F, No. 363 Fu Shing North Road Taipei, Taiwar Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.

1 harbourFront Avenue, #06-10, keppel Bay Tower, Singapore 098632
Tel: +65-6273-0200, Fax: +65-6278-8019
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Renesas Electronics Korea Co., Ltd. 11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea Tel: 482-2-588-3737, Fax: 482-2-558-5141